

UNITED STATES PATENT AND TRADEMARK OFFICE  
**CERTIFICATE OF CORRECTION**

PATENT NO. : 6,896,969 B2  
DATED : May 24, 2005  
INVENTOR(S) : Alan R. Reinberg

Page 1 of 2

It is certified that error appears in the above-identified patent and that said Letters Patent is hereby corrected as shown below:

Column 2.

Lines 31 and 32, reads "low temperatures (i.e., approximately 400° C. and is therefore not damaging to the underlying polysilicon conductive" should read -- low temperatures (i.e., approximately 400° C and is therefore not damaging to the underlying polysilicon conductive --.

Column 4.

Line 4, reads "a temperature ranging from 100° to 600° C. at a pressure" should read -- a temperature ranging from 100° to 600° C at a pressure --.

Column 5.

Line 37, reads "V<sub>2</sub>O<sub>3</sub>, V<sub>2</sub>O<sub>5</sub>, VO<sub>2</sub>, V<sub>2</sub>O<sub>5</sub>, VO<sub>2</sub>, WO<sub>3</sub>, Y<sub>2</sub>O<sub>3</sub>, ZnO, and ZrO<sub>2</sub>" should read -- V<sub>2</sub>O<sub>3</sub>, V<sub>2</sub>O<sub>5</sub>, VO<sub>2</sub>, V<sub>2</sub>O<sub>5</sub>, VO<sub>2</sub>, WO<sub>3</sub>, Y<sub>2</sub>O<sub>3</sub>, ZnO, and ZrO<sub>2</sub> --.

Column 8.

Line 15, reads "point of 16.8° C. (62.2° F.). A small amount of inhibitor" should read -- point of 16.8° C (62.2° F). A small amount of inhibitor --.

Line 18, reads "higher melting beta- (m.p. 32.5° C.) and alpha- (m.p.)" should read -- higher melting beta- (m.p. 32.5° C) and alpha- (m.p. --.

Line 19, reads "62.3° C. forms of sulfur trioxide. Gamma-form sulfur" should read -- 62.3° C forms of sulfur trioxide. Gamma-form sulfur --.

Line 22, reads "has a melting point of greater than 16.8° C., the sulfur" should read -- has a melting point of greater than 16.8° C, the sulfur --.

Column 9.

Line 34, reads "between 100° C. to 600° C.; and the time of exposure, given" should read -- between 100° C to 600° C; and the time of exposure, given --.

Column 11.

Line 63, reads "600° C. and the sulfur trioxide is preferably in contact with" should read -- 600° C and the sulfur trioxide is preferably in contact with --.

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Column 12.

Line 53, reads "V<sub>2</sub>O<sub>5</sub>, VO<sub>2</sub> and ZnO" should read -- VaO<sub>5</sub>, VO<sub>2</sub>, and ZnO --.

Line 63, reads "comprised of substoichiometric tantalum oxide." should read  
-- comprised of substoichiometric tantalum oxide. --.

Line 67, reads "comprised of substoichiometric oxide." should read -- comprised of  
substoichiometric oxide. --.

Column 13.

Line 4, reads "temperature ranging from 100° C. to 600° C." should read -- temperature  
ranging from 100° C to 600° C. --.

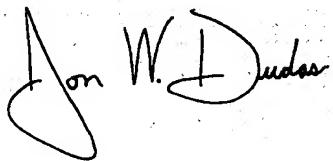
Column 14.

Lines 5 and 6, reads "is comprised of substoichiometric tantalum oxide layer having a  
thickness of 5 to 200 Angstroms, wherein the sulfur" should read -- is comprised of  
substoichiometric tantalum oxide layer having a thickness of 5 to 200 Angstroms,  
wherein the sulfur --.

Lines 7 and 8, reads "trioxide is gaseous sulfur trioxide, wherein the substoichiometric  
tantalum oxide layer is disposed on a conductive" should read -- trioxide is gaseous  
sulfur trioxide, wherein the substoichiometric tantalum oxide layer is disposed on a  
conductive --.

Signed and Sealed this

Twenty-eighth Day of March, 2006



JON W. DUDAS  
Director of the United States Patent and Trademark Office